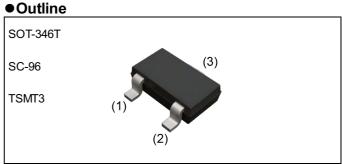
Pch -30V -4A Small Signal MOSFET

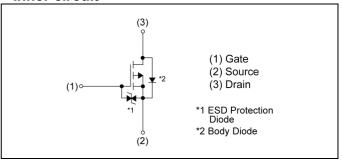
| V <sub>DSS</sub>           | -30V |
|----------------------------|------|
| R <sub>DS(on)</sub> (Max.) | 45mΩ |
| I <sub>D</sub>             | ±4A  |
| P <sub>D</sub>             | 1.0W |



### Features

- 1) Low on resistance
- 2) Built-in G-S Protection Diode
- 3) Small Surface Mount Package (TSMT3)
- 4) Pb-free lead plating; RoHS compliant

## ●Inner circuit



Packaging specifications

|      | Packing                   | Embossed<br>Tape |
|------|---------------------------|------------------|
|      | Reel size (mm)            | 180              |
| Туре | Tape width (mm)           | 8                |
|      | Basic ordering unit (pcs) | 3000             |
|      | Taping code               | TL               |
|      | Marking                   | UG               |

# Application

DC/DC converters

# ● **Absolute maximum ratings** (T<sub>a</sub> = 25°C ,unless otherwise specified)

| Parameter  | Symbol             | Value       | Unit |
|--|--------------------|-------------|------|
| Drain - Source voltage                           | V <sub>DSS</sub>   | -30         | V    |
| Continuous drain current                         | I <sub>D</sub>     | ±4          | А    |
| Pulsed drain current                             | I <sub>DP</sub> *1 | ±16         | А    |
| Gate - Source voltage                            | V <sub>GSS</sub>   | ±20         | V    |
| Dower discination                                | P <sub>D</sub> *2  | 1.0         | W    |
| Power dissipation                                | P <sub>D</sub> *3  | 0.7         | W    |
| Junction temperature                             | Tj                 | 150         | °C   |
| Operating junction and storage temperature range | T <sub>stg</sub>   | -55 to +150 | °C   |

# ●Thermal resistance

| Deremeter                                      | Cumb ol              | Values |      |      | Linit |
|--|----------------------|--------|------|------|-------|
| Parameter                                      | Symbol               | Min.   | Тур. | Max. | Unit  |
| The world reciptors of investigation amplicant | R <sub>thJA</sub> *2 | -      | -    | 125  | °C/W  |
| Thermal resistance, junction - ambient         | R <sub>thJA</sub> *3 | -      | -    | 178  | °C/W  |

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

| Parameter                                      | Symbol                                    | Conditions                                   | Values |       |      | Unit  |  |
|--|---|--|--------|-------|------|-------|--|
|  | Symbol                                    | Conditions                                   | Min.   | Тур.  | Max. | Offic |  |
| Drain - Source breakdown<br>voltage            | V <sub>(BR)DSS</sub>                      | $V_{GS} = 0V$ , $I_D = -1mA$                 | -30    | -     | -    | V     |  |
| Breakdown voltage temperature coefficient      | $\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$ | I <sub>D</sub> = -1mA<br>referenced to 25°C  | -      | -24.1 | -    | mV/°C |  |
| Zero gate voltage drain current                |   | V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V | 1      | 1     | -1   | μA    |  |
| Gate - Source leakage current                  | I <sub>GSS</sub>                          | $V_{GS} = \pm 20V, V_{DS} = 0V$              | 1      | 1     | ±10  | μA    |  |
| Gate threshold voltage                         | V <sub>GS(th)</sub>                       | $V_{DS} = -10V, I_{D} = -1mA$                | -1.0   | -     | -2.5 | V     |  |
| Gate threshold voltage temperature coefficient | $\frac{\DeltaV_{GS(th)}}{\DeltaT_j}$      | I <sub>D</sub> = -1mA<br>referenced to 25°C  | -      | 3.3   | -    | mV/°C |  |
|  |   | V <sub>GS</sub> = -10V, I <sub>D</sub> = -4A | -      | 32    | 45   |       |  |
| Static drain - source on - state resistance    | R <sub>DS(on)</sub> *4                    | $V_{GS} = -4.5V, I_D = -2A$                  | 1      | 45    | 63   | mΩ    |  |
|  |   | $V_{GS} = -4V, I_D = -2A$                    | 1      | 52    | 72   |       |  |
| Gate resistance                                | $R_G$                                     | f = 1MHz, open drain                         | 1      | 13    | 1    | Ω     |  |
| Forward Transfer<br>Admittance                 | Y <sub>fs</sub>  *4                       | V <sub>DS</sub> = -10V, I <sub>D</sub> = -4A | 2.7    | 1     | -    | S     |  |

<sup>\*1</sup> Pw  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

<sup>\*2</sup> Mounted on a ceramic boad (30×30×0.8mm)

<sup>\*3</sup> Mounted on a FR4 (25×25×0.8mm)

<sup>\*4</sup> Pulsed

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

| Darameter  | Symbol                | Conditions                          |      | Unit |      |      |
|--|-----------------------|-------------------------------------|------|------|------|------|
| Parameter  | Symbol                | Conditions                          | Min. | Тур. | Max. | Unit |
| Input capacitance  | C <sub>iss</sub>      | V <sub>GS</sub> = 0V                | -    | 1000 | -    | _    |
| Output capacitance C <sub>oss</sub>                            |                       | V <sub>DS</sub> = -10V              | -    | 150  | -    | pF   |
| Reverse transfer capacitance                                   | C <sub>rss</sub>      | f = 1MHz                            | -    | 130  | 1    |      |
| Turn - on delay time   | t <sub>d(on)</sub> *4 | $V_{DD} \simeq -15V, V_{GS} = -10V$ | -    | 15   | 1    |      |
| Rise time  | t <sub>r</sub> *4     | I <sub>D</sub> = -2A                | -    | 30   | -    | no   |
| Turn - off delay time ${\mathsf t_{\mathsf d(off)}}^{\star 4}$ |                       | $R_L \simeq 7.5\Omega$              | _    | 85   | 1    | ns   |
| Fall time  | t <sub>f</sub> *4     | $R_G = 10\Omega$                    | -    | 45   | -    |      |

# • Gate charge characteristics $(T_a = 25^{\circ}C)$

|                      | \ a                | ,   |      |        |      |       |
|----------------------|--------------------|---|------|--------|------|-------|
| Parameter            | Symbol             | abol Conditions -   |      | Values |      | Unit  |
| raianietei           | Symbol             | Conditions  | Min. | Тур.   | Max. | Offic |
| Total gate charge    | Qg*4               | V <sub>DD</sub> ≃ -15V.                                   | -    | 10.5   | -    |       |
| Gate - Source charge | Q <sub>gs</sub> *4 | $V_{DD} \simeq -15V$ ,<br>$I_D = -4A$ ,<br>$V_{GS} = -5V$ | -    | 3.0    | -    | nC    |
| Gate - Drain charge  | Q <sub>gd</sub> *4 | $V_{GS} = -5V$  | -    | 3.3    | -    |       |

# ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

| Darameter                  | Symbol             | Conditions                                 | Values |      |      | Unit  |  |
|----------------------------|--------------------|--|--------|------|------|-------|--|
| Parameter                  | Symbol             | Conditions                                 | Min.   | Тур. | Max. | Uriit |  |
| Continuous forward current | I <sub>S</sub>     | T = 25°C                                   | -      | -    | -0.8 | Α     |  |
| Pulse forward current      | I <sub>SP</sub> *1 | - T <sub>a</sub> = 25°C                    | -      | -    | -16  | Α     |  |
| Forward voltage            | V <sub>SD</sub> *4 | V <sub>GS</sub> = 0V, I <sub>S</sub> = -4A | -      | -    | -1.2 | V     |  |

Fig.1 Power Dissipation Derating Curve

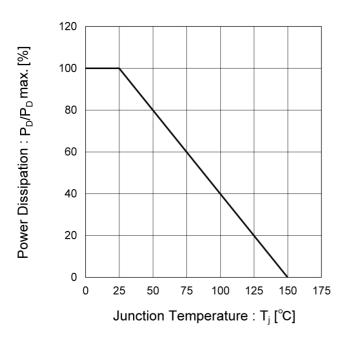
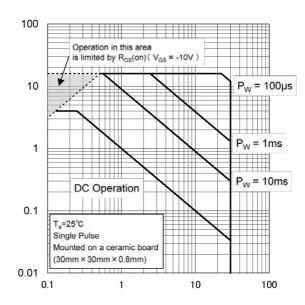


Fig.2 Maximum Safe Operating Area



Drain Current: -l<sub>D</sub> [A]

Drain - Source Voltage: -VDS [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

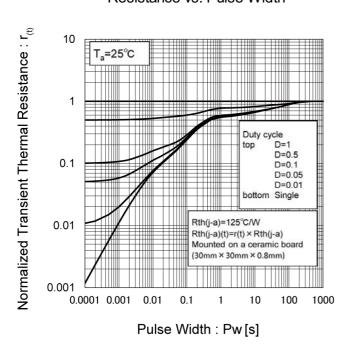


Fig.4 Single Pulse Maximum Power dissipation

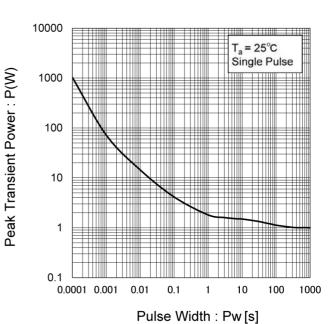
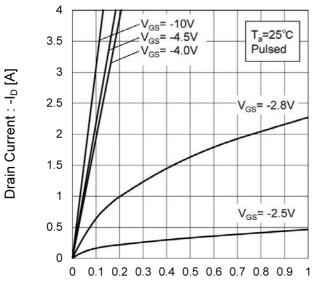


Fig.5 Typical Output Characteristics(I)



Drain - Source Voltage : -V<sub>DS</sub> [V]

Fig.6 Typical Output Characteristics(II)

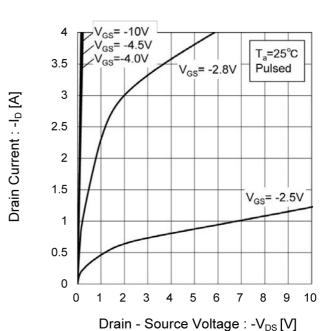


Fig.7 Breakdown Voltage vs.
Junction Temperature

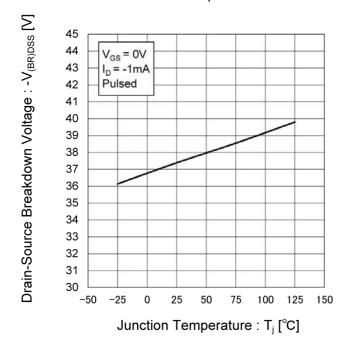


Fig.8 Typical Transfer Characteristics

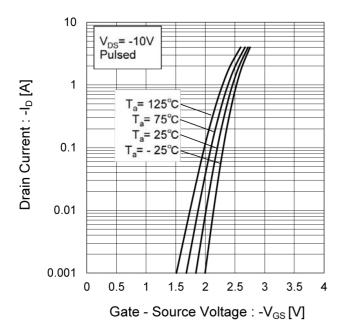


Fig.9 Gate Threshold Voltage vs.
Junction Temperature

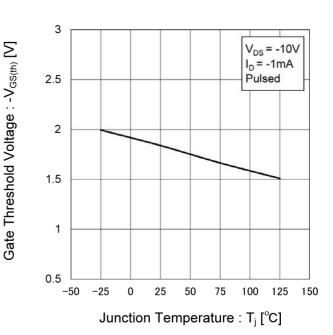
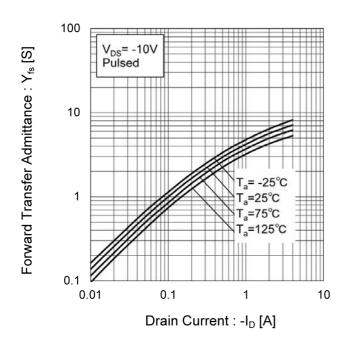


Fig.10 Forward Transfer Admittance vs.
Drain Current



6/11

Fig.11 Drain Current Derating Curve

120 100 Drain Current Dissipation 80 : I<sub>D</sub>/I<sub>D</sub>max. [%] 60 40 20 0 -25 0 25 50 75 100 125 150 Junction Temperature : T<sub>j</sub> [°C]

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

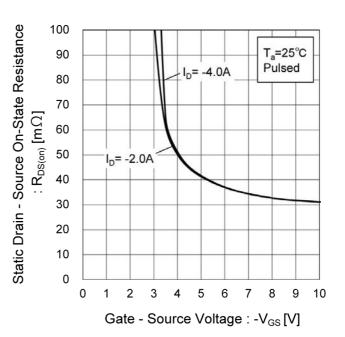


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

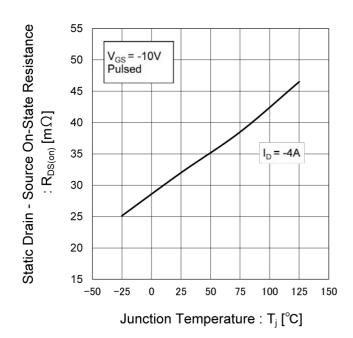


Fig.14 Static Drain - Source On - State
Resistance vs. Drain Current (I)

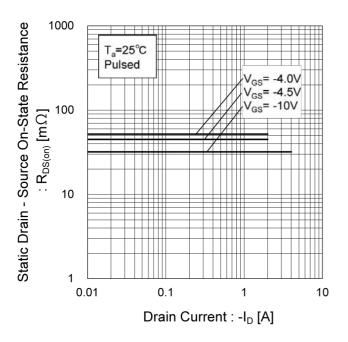


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (II)

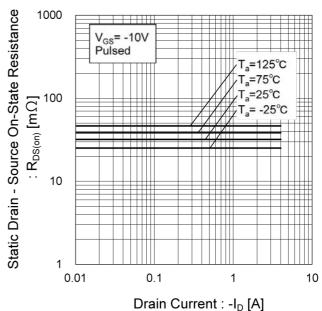


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current (III)

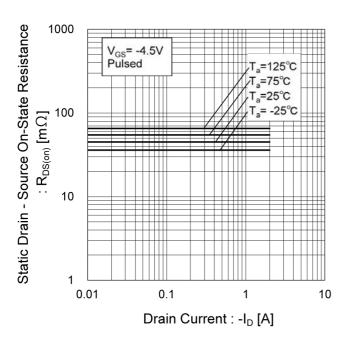


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current (IV)

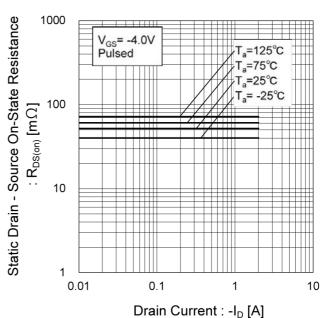


Fig.18 Typical Capacitance vs.

Drain - Source Voltage

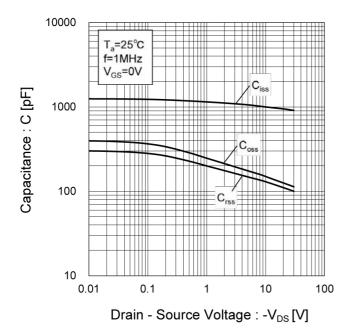


Fig.19 Switching Characteristics

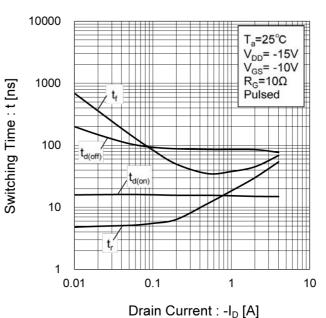


Fig.20 Dynamic Input Characteristics

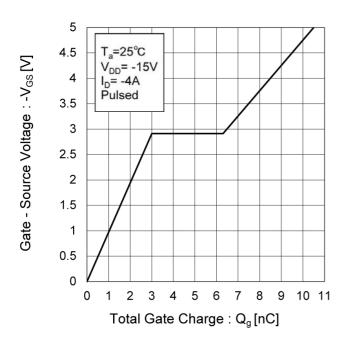
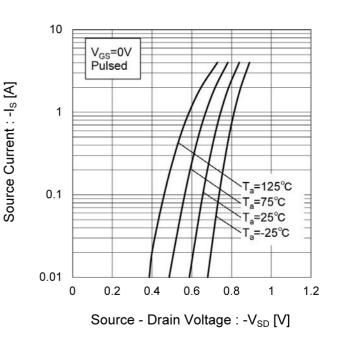


Fig.21 Source Current vs.

Source Drain Voltage



### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

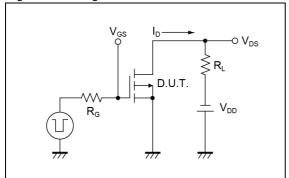


Fig.2-1 Gate Charge Measurement Circuit

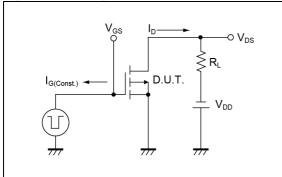


Fig.1-2 Switching Waveforms

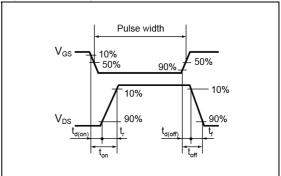
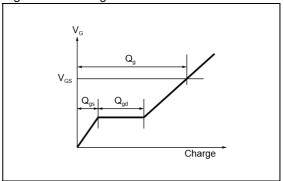


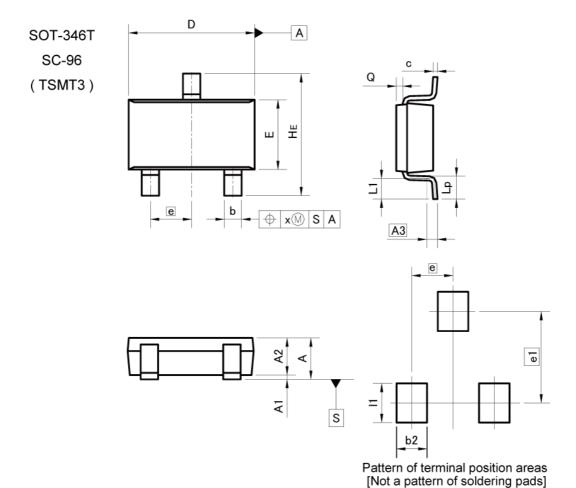
Fig.2-2 Gate Charge Waveform



### Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

# Dimensions



| DIM | MILIM | ETERS | INC          | HES   |
|-----|-------|-------|--------------|-------|
| DIM | MIN   | MAX   | MIN          | MAX   |
| Α   | =0    | 1.00  |              | 0.039 |
| A1  | 0.00  | 0.10  | 0.000        | 0.004 |
| A2  | 0.75  | 0.95  | 0.030        | 0.037 |
| A3  | 0.:   | 25    | 0.0          | 10    |
| b   | 0.35  | 0.50  | 0.014        | 0.020 |
| С   | 0.10  | 0.26  | 0.004        | 0.010 |
| D   | 2.80  | 3.00  | 0.110        | 0.118 |
| E   | 1.50  | 1.80  | 0.059        | 0.071 |
| е   | 0.9   | 0.95  |              | 37    |
| HE  | 2.60  | 3.00  | 0.102        | 0.118 |
| L1  | 0.30  | 0.60  | 0.012        | 0.024 |
| Lp  | 0.40  | 0.70  | 0.016        | 0.028 |
| Q   | 0.05  | 0.25  | 0.002        | 0.010 |
| x   | 776   | 0.20  | <del>-</del> | 0.008 |

| DIM - | MILIM | MILIMETERS |                 | HES   |
|-------|-------|------------|-----------------|-------|
| DIM   | MIN   | MAX        | MIN             | MAX   |
| b2    |       | 0.70       | 57/2            | 0.028 |
| e1    | 2.    | 10         | 0.0             | 083   |
| 11    | =1    | 0.90       | <del>77</del> 2 | 0.035 |

Dimension in mm/inches



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Our Products are designed and manufactured for application in ordinary electronic equipments (such as AV equipment, OA equipment, telecommunication equipment, home electronic appliances, amusement equipment, etc.). If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (Note 1), transport equipment, traffic equipment, aircraft/spacecraft, nuclear power controllers, fuel controllers, car equipment including car accessories, safety devices, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

| JÁPAN   | USA      | EU         | CHINA    |
|---------|----------|------------|----------|
| CLASSⅢ  | CLASSIII | CLASS II b | CLASSⅢ   |
| CLASSIV | CLASSIII | CLASSⅢ     | CLASSIII |

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  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### **Precaution for Mounting / Circuit board design**

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

#### **Precautions Regarding Application Examples and External Circuits**

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
  may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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